

# isc Silicon PNP Power Transistor

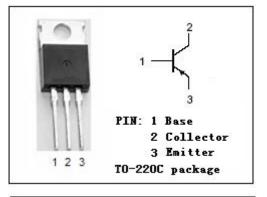
# 2SB1064

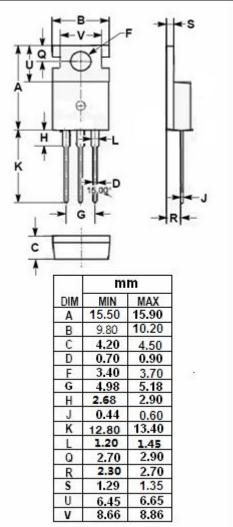
### DESCRIPTION

- Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= -1.0V(Max)@I<sub>C</sub>= -2A
- Wide Area of Safe Operation
- Complement to Type 2SD1505
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Designed for low frequency power amplifier applications.





## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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SYMBOL	PARAMETER	UNIT			
V <sub>CBO</sub>	Collector-Base Voltage	V			
Vceo	Collector-Emitter Voltage	-50	V		
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V		
lc	Collector Current-Continuous	-3	А		
I <sub>CM</sub>	Collector Current-Peak	-4.5	А		
Pc	Total Power Dissipation @ T <sub>a</sub> =25℃	1.5	W		
	Total Power Dissipation @ T <sub>C</sub> =25℃	30			
TJ	Junction Temperature	150	°C		
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C		



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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA ; I <sub>B</sub> = 0	-50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -50 μ A; I <sub>E</sub> = 0	-60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -50 μ A; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-1.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-1.0	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -3V	60		320	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -5V		70		MHz
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f= 1MHz		50		pF

### h<sub>FE</sub> Classifications

D	Е	F
60-120	100-200	160-320

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